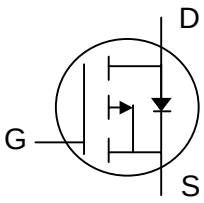
P-channel Enhancement-mode Power MOSFET

Simple Drive Requirement

Low On-resistance

Fast Switching Performance

RoHS-compliant, halogen-free

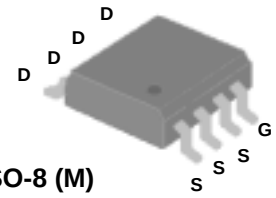


BV_{DSS}	-30V
$R_{DS(ON)}$	8.2mΩ
I_D	-14A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP4405GM-HF-3 is in the SO-8 package, which is widely used for commercial and industrial surface-mount applications, and is well suited for low voltage applications such as DC/DC converters.



SO-8 (M)

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D at T_C=25°C	Continuous Drain Current[3]	-14	A
I_D at T_C= 70°C	Continuous Drain Current[3]	-11.3	A
I_{DM}	Pulsed Drain Current[1]	-50	A
P_D at T_C=25°C	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient	50	°C/W

Ordering Information

AP4405GM-HF-3TR : in RoHS-compliant halogen-free SO-8, shipped on tape and reel (3000 pcs/reel)

Electrical Specifications at T_j=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V, I_D=-13A	-	-	8.2	mΩ
		V_{GS}=-4.5V, I_D=-10A	-	-	15	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-1.0	-	-3.0	V
g_{fs}	Forward Transconductance	V_{DS}=-10V, I_D=-10A	-	10	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=-24V, V_{GS}=0V	-	-	-1	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=-24V, V_{GS}=0V	-	-	-25	uA
I_{GSS}	Gate-Source Leakage	V_{GS} = ±20V	-	-	±100	nA
Q_g	Total Gate Charge[2]	I_D=-13A	-	44	70	nC
Q_{gs}	Gate-Source Charge	V_{DS}=-24V	-	7	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=-4.5V	-	28	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=-15V	-	13	-	ns
t_r	Rise Time	I_D=-1A	-	11	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω, V_{GS}=-10V	-	64	-	ns
t_f	Fall Time	R_D=15Ω	-	42	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	3400	5440	pF
C_{oss}	Output Capacitance	V_{DS}=-25V	-	520	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	455	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=-2.0A, V_{GS}=0V	-	-	-1.2	V
t_{rr}	Reverse Recovery Time[2]	I_S=-13A, V_{GS}=0V	-	37	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	35	-	nC

Notes:

1.Pulse width limited by maximum junction temperature.

2.Pulse test - pulse width ≤ 300μs , duty cycle ≤ 2%

3.Surface mounted on 1 in^2 copper pad of FR4 board; 125°C/W on minimum copper pad.

Typical Electrical Characteristics

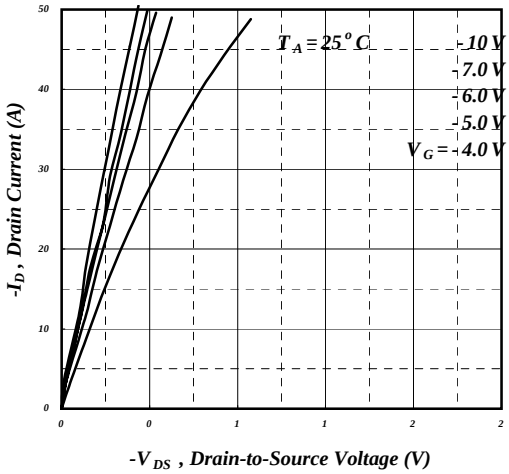


Fig 1. Typical Output Characteristics

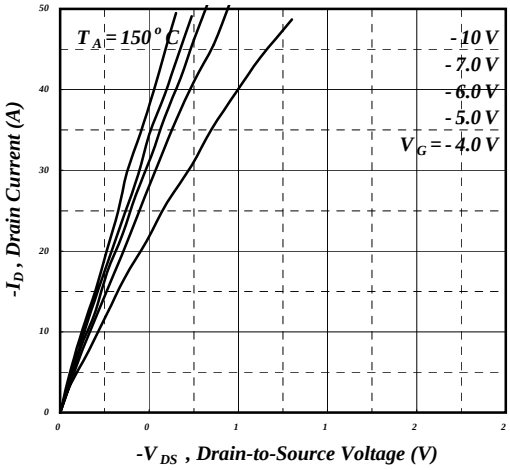


Fig 2. Typical Output Characteristics

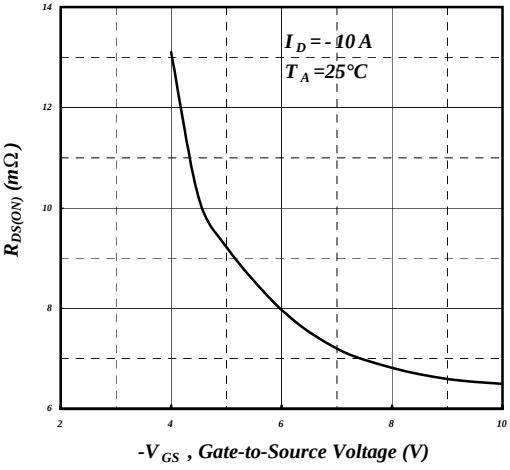


Fig 3. On-Resistance vs. Gate Voltage

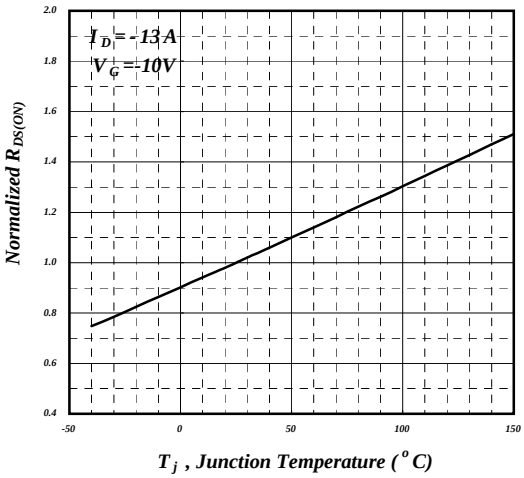


Fig 4. Normalized On-Resistance vs. Junction Temperature

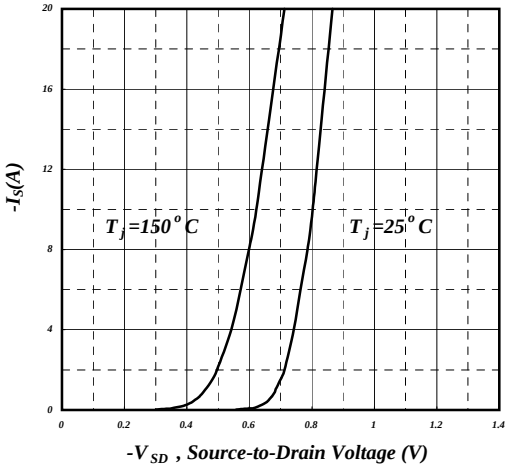


Fig 5. Forward Characteristic of Reverse Diode

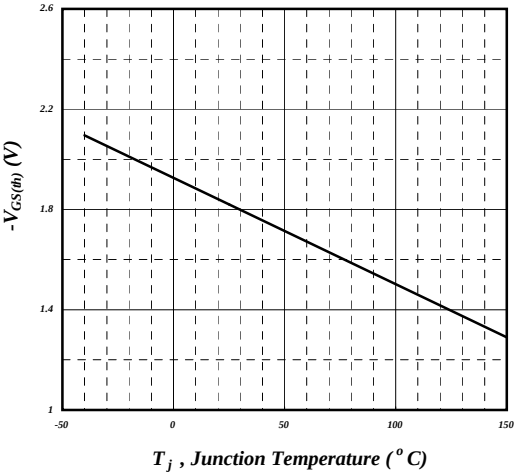


Fig 6. Gate Threshold Voltage vs. Junction Temperature

Typical Electrical Characteristics (cont.)

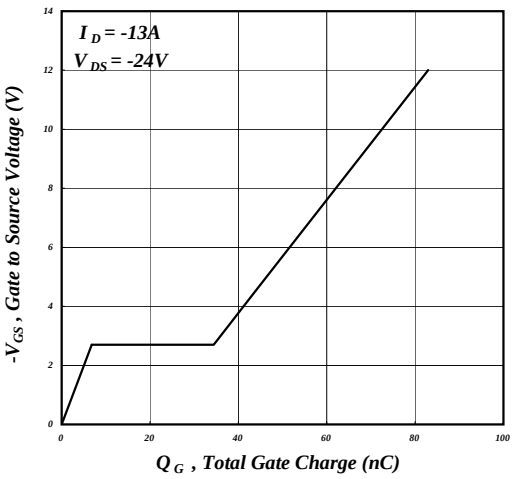


Fig 7. Gate Charge Characteristics

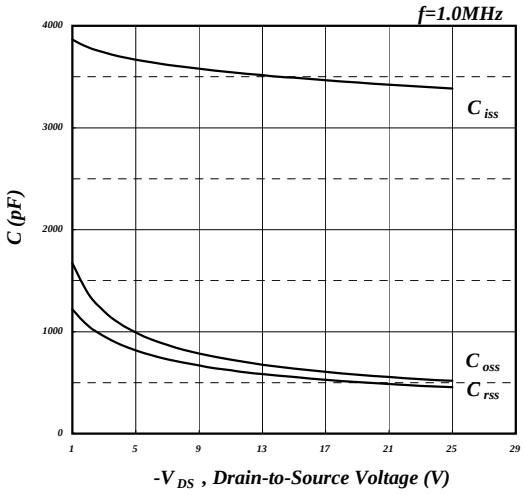


Fig 8. Typical Capacitance Characteristics

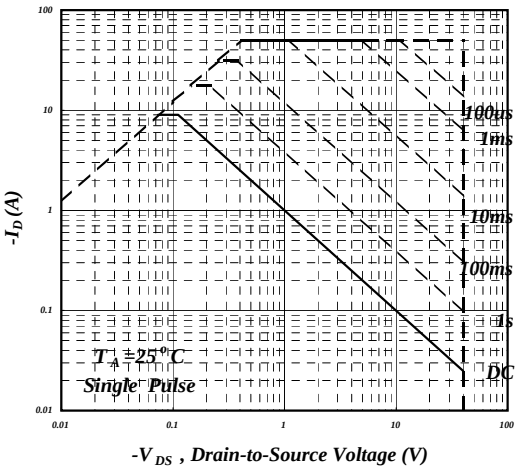


Fig 9. Maximum Safe Operating Area

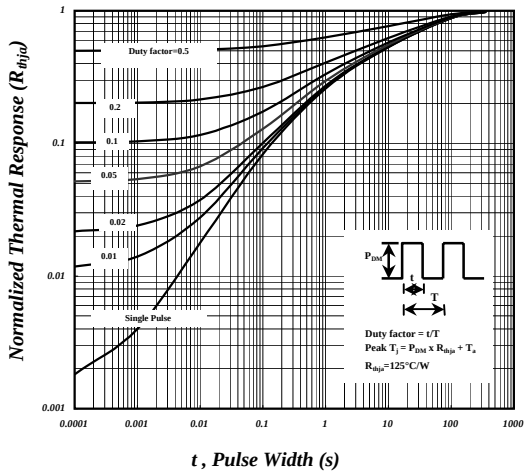


Fig 10. Effective Transient Thermal Impedance

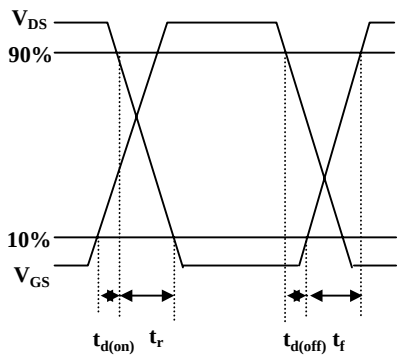


Fig 11. Switching Time Waveforms

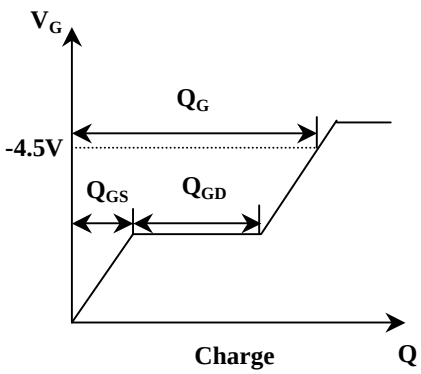
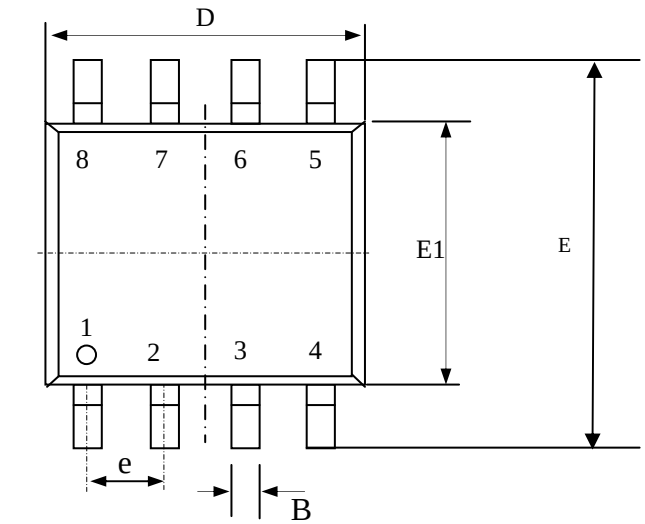
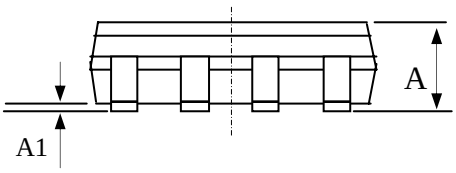


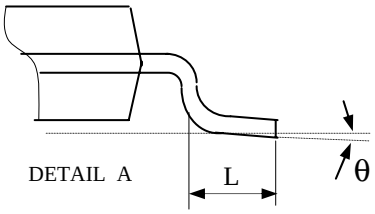
Fig 12. Gate Charge Waveform

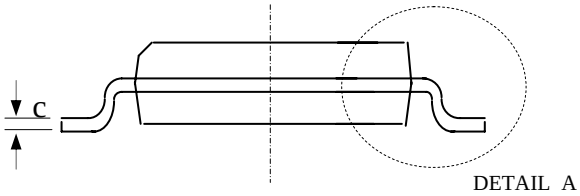
Package Dimensions: SO-8



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.18	0.25
B	0.33	0.41	0.51
C	0.19	0.22	0.25
D	4.80	4.90	5.00
E1	3.80	3.90	4.00
E	5.80	6.15	6.50
L	0.38	0.71	1.27
θ	0	4.00	8.00
e	1.27 TYP		







1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information: